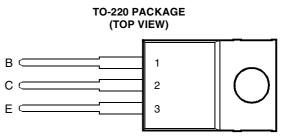
BOURNS®

BD744, BD744A, BD744B, BD744C PNP SILICON POWER TRANSISTORS

- Designed for Complementary Use with the BD743 Series
- 90 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- 20 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
	BD744		-50	
Collector base veltage $(I = 0)$	BD744A	V	-70	v
Collector-base voltage ($I_E = 0$)	BD744B	V _{CBO}	-90	v
	BD744C		-110	
	BD744		-45	
Collector-emitter voltage ($I_B = 0$)	BD744A	N	-60	v
	BD744B	V _{CEO}	-80	v
	BD744C		-100	
Emitter-base voltage	V _{EBO}	-5	V	
Continuous collector current			-15	A
Peak collector current (see Note 1)	I _{CM}	-20	A	
Continuous base current	I _B	-5	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note	P _{tot}	90	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W
Unclamped inductive load energy (see Note 4)	½Ll _C ²	90	mJ	
Operating free air temperature range			-65 to +150	°C
Operating junction temperature range		Тj	-65 to +150	°C
Storage temperature range		T _{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds			260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

2. Derate linearly to 150°C case temperature at the rate of 0.72 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.

PRODUCT INFORMATION

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electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS				MIN	ТҮР	MAX	UNIT
	Collector-emitter	I _C = -30 mA	I _B = 0	(see Note 5)	BD744 BD744A	-45 -60			
V _{(BR)CEO} breakdown vo					BD744B	-80			V
	Stoallaotti toilago				BD744C	-100			
		V _{CE} = -50 V	$V_{BE} = 0$		BD744			-0.1	
		V _{CE} = -70 V	$V_{BE} = 0$		BD744A			-0.1	
		V _{CE} = -90 V	$V_{BE} = 0$		BD744B			-0.1	
	Collector cut-off	V _{CE} = -110 V	$V_{BE} = 0$		BD744C			-0.1	
I _{СВО}	current	V _{CE} = -50 V	$V_{BE} = 0$	T _C = 125°C	BD744			-5	mA
		V _{CE} = -70 V	$V_{BE} = 0$	T _C = 125°C	BD744A			-5	
		V _{CE} = -90 V	$V_{BE} = 0$	T _C = 125°C	BD744B			-5	
		V _{CE} = -110 V	$V_{BE} = 0$	T _C = 125°C	BD744C			-5	
1	Collector cut-off	V _{CE} = -30 V	I _B = 0		BD744/744A			-0.1	mA
ICEO	current	V _{CE} = -60 V	$I_B = 0$		BD744B/744C			-0.1	ma
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	$I_{\rm C} = 0$					-0.5	mA
	Forward current transfer ratio	$V_{CE} = -4 V$	I _C = -1 A			40			
h _{FE}		$V_{CE} = -4 V$	I _C = -5 A	(see Notes 5 ar	nd 6)	20		150	
transier ra		$V_{CE} = -4 V$	I _C = -15 A			5			
Varia	Collector-emitter	I _B = -0.5 A	I _C = -5 A	(see Notes 5 ar	(see Notes 5 and 6)			-1	V
V _{CE(sat)}	saturation voltage	I _B = -5 A		(300 10000 0 0	(see notes 5 and 6)			-3	v
V _{BE}	Base-emitter	$V_{CE} = -4 V$	-	(see Notes 5 and 6)				-1	V
* BE	voltage	$V_{CE} = -4 V$	I _C = -15 A					-3	v
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -1 A	f = 1 kHz		25			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	$I_{\rm C} = -1 \rm A$	f = 1 MHz		5			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R _{θJC}	Junction to case thermal resistance			1.4	°C/W
R _{θJA}	Junction to free air thermal resistance			62.5	°C/W

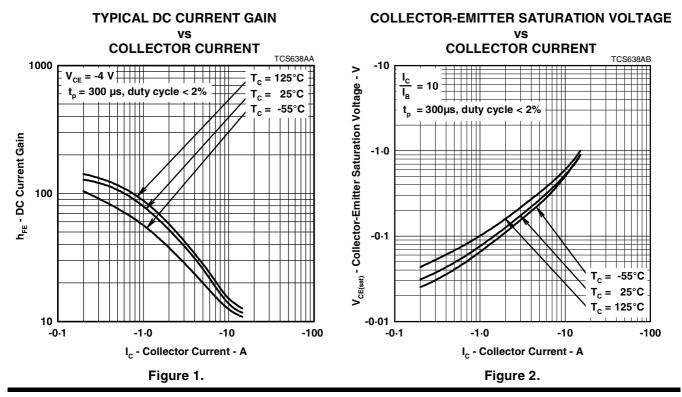
resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]				ТҮР	MAX	UNIT
t _d Delay time					20		ns
t _r Rise time	I _C = -5 A	I _{B(on)} = -0.5 A	$I_{B(off)} = 0.5 A$		120		ns
t _s Storage time	$V_{BE(off)} = 4.2 V$	$R_L = 6 \Omega$	t_p = 20 µs, dc \leq 2%		600		ns
t _f Fall time					300		ns

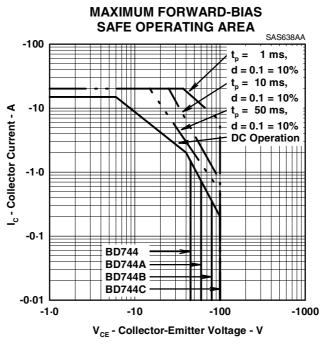
[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS









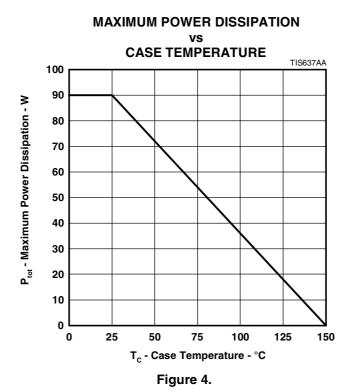
PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

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THERMAL INFORMATION





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